



## BUL312FP

### HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

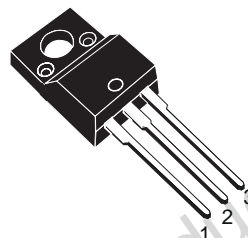
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C
- LARGE RBSOA
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING

#### APPLICATIONS

- HORIZONTAL DEFLECTION FOR TV
- SMPS
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING

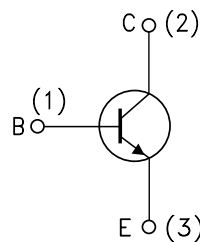
#### DESCRIPTION

The BUL312FP is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability. It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.



TO-220FP

#### INTERNAL SCHEMATIC DIAGRAM



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	1150	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	500	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	9	V
$I_C$	Collector Current	5	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	10	A
$I_B$	Base Current	3	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	4	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	36	W
$V_{isol}$	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	1500	V
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

## THERMAL DATA

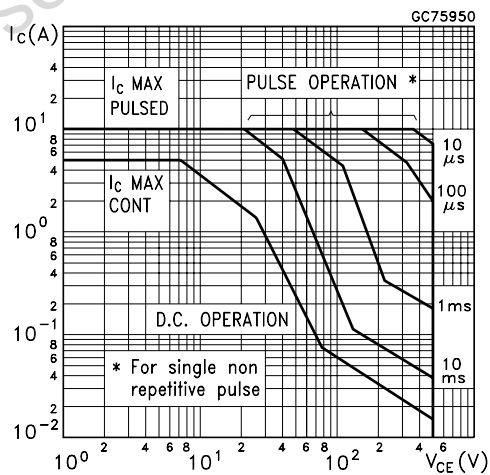
$R_{thj-case}$	Thermal Resistance Junction-Case	Max	3.5	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	62.5	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$  unless otherwise specified)

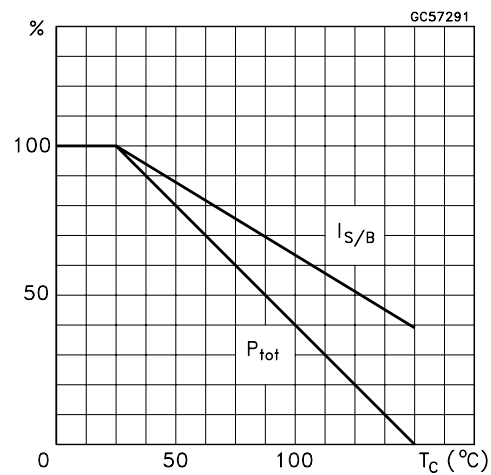
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CES}$	Collector Cut-off Current ( $V_{BE} = 0$ )	$V_{CE} = 1150 V$ $V_{CE} = 1150 V \quad T_j = 125^{\circ}C$			1 2	$mA$ $mA$
$I_{CEO}$	Collector Cut-off Current ( $I_B = 0$ )	$V_{CE} = 500 V$			250	$\mu A$
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage ( $I_B = 0$ )	$I_C = 100 mA \quad L = 25 mH$	500			$V$
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	$I_E = 10 mA$	10			$V$
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 1 A \quad I_B = 0.2 A$ $I_C = 2 A \quad I_B = 0.4 A$ $I_C = 3 A \quad I_B = 0.6 A$			0.5 0.7 1.1	$V$ $V$ $V$
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 1 A \quad I_B = 0.2 A$ $I_C = 2 A \quad I_B = 0.4 A$ $I_C = 3 A \quad I_B = 0.6 A$			1 1.1 1.2	$V$ $V$ $V$
$h_{FE}^*$	DC Current Gain	$I_C = 10 mA \quad V_{CE} = 5 V$ $I_C = 3 A \quad V_{CE} = 2.5 V$	8 8		13.5	
$t_s$ $t_f$	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 2 A \quad I_{B1} = 0.4 A$ $V_{BE(off)} = -5 V \quad R_{BB} = 0 \Omega$ $V_{CL} = 250 V \quad L = 200 \mu H$ (see fig. 1)		1.2 80	1.9 160	$\mu s$ $ns$
$t_s$ $t_f$	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 2 A \quad I_{B1} = 0.4 A$ $V_{BE(off)} = -5 V \quad R_{BB} = 0 \Omega$ $V_{CL} = 250 V \quad L = 200 \mu H$ $T_j = 125^{\circ}C$ (see fig. 1)		1.8 150		$\mu s$ $ns$

\* Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %

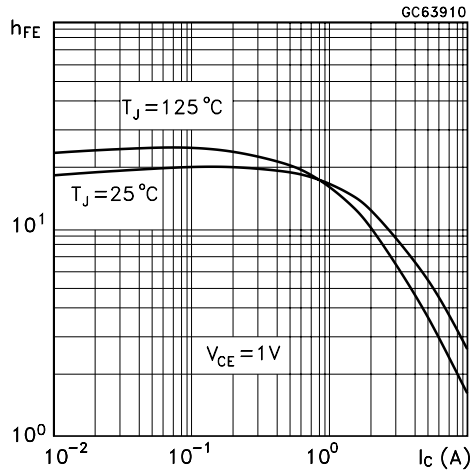
## Safe Operating Areas



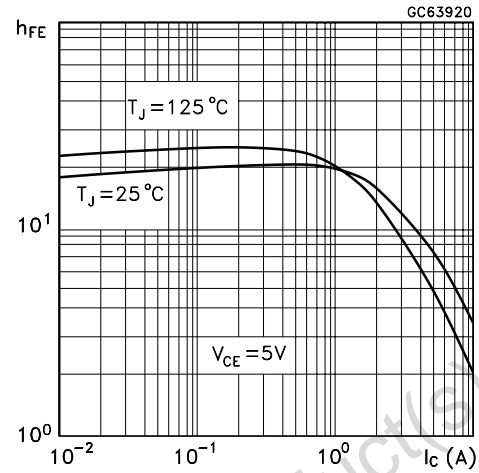
## Derating Curve



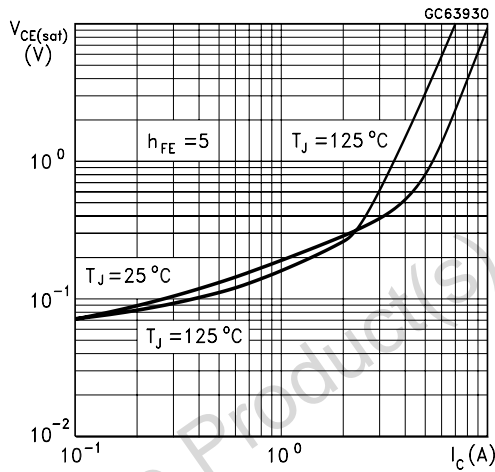
DC Current Gain



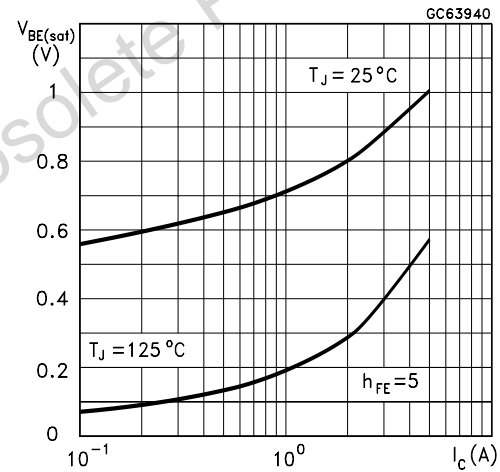
DC Current Gain



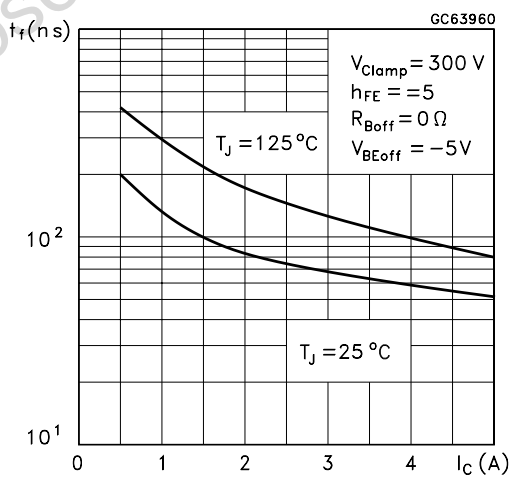
Collector Emitter Saturation Voltage



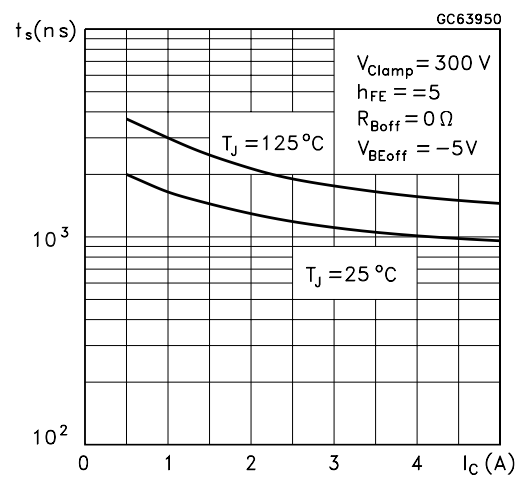
Base Emitter Saturation Voltage



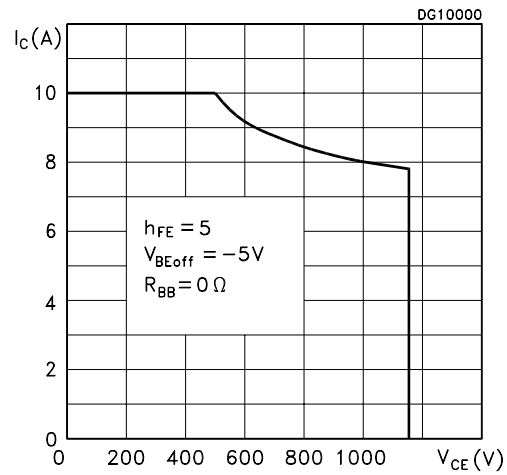
Inductive Fall Time



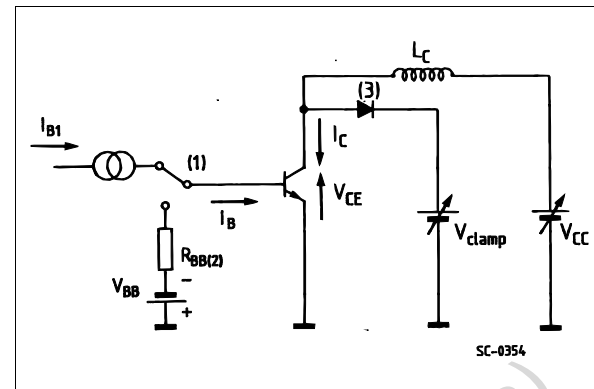
Inductive Storage Time



## Reverse Biased SOA



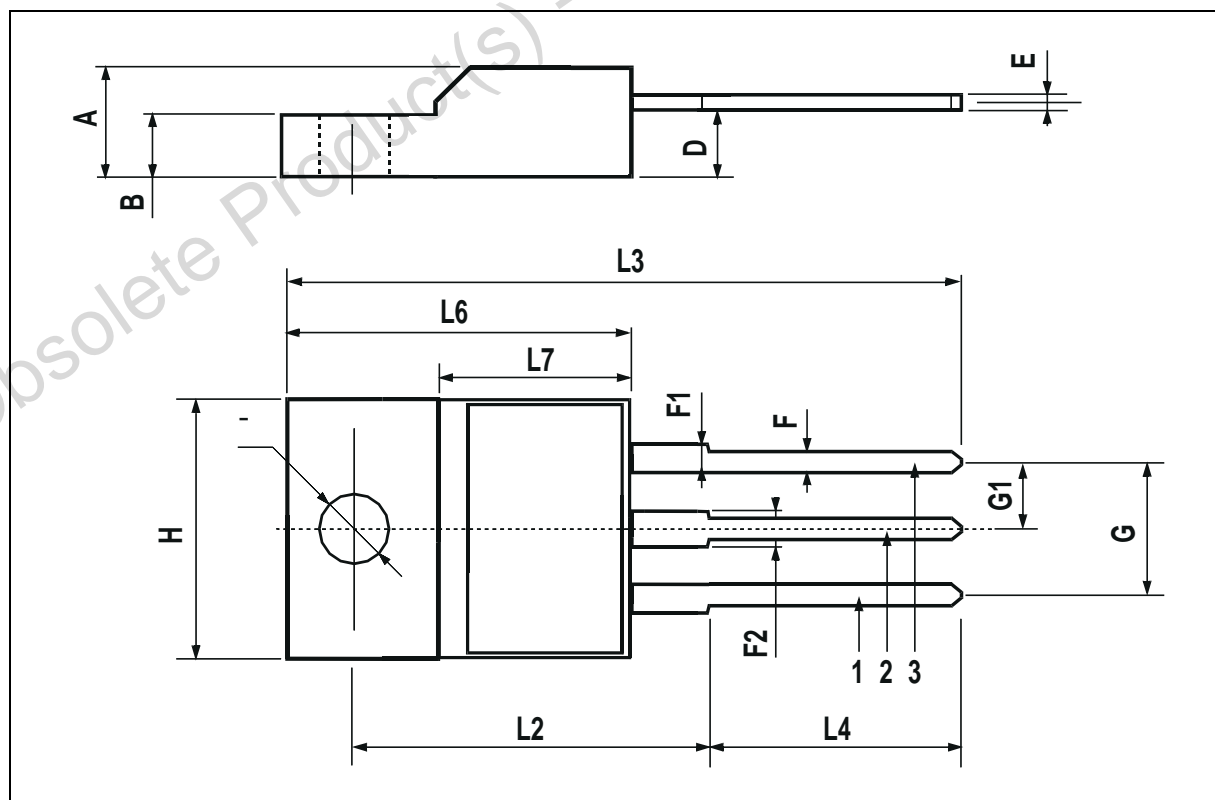
**Figure 1:** Inductive Load Switching Test Circuit



- (1) Fast electronic switch
- (2) Non-inductive Resistor
- (3) Fast recovery rectifier

## TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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